mail

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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GlobalPower sicDevices 1200V SiC Schottky Diode



GDP30D120B

VDC	1200 V
Q _c	52/104 nC*
F (V _F =1.5V)	15/30 A*
	*Per Leg/Device

Amp+[™] Applications

• Switch mode power supplies

• Power factor correction

Motor drives

Diode snubber

Amp+[™] Features

- High surge current capable
- Zero reverse recovery current
- High bandwidth
- Fast, temperature-independent switching



Amp+[™] Benefits

- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices with thermal stability

Part #	Package	Marking
GDP30D120B	TO-247-3	GDP30D120



Maximum Rating Per Leg	Symbol	Conditions	Value	Unit	
		T _C =25 °C, T _j =175 °C	28		
Continuous forward current	I _F	T _C =125 °C, T _j =175 °C	15		
		T _C =150 °C, T _j =175 °C	10		
Surge non-repetitive forward current	1	T _C =25 °C, t _p =8.3 ms	120	A	
sine halfwave	'F,SM	T _C =150 °C, t _p =8.3 ms	75		
Non-repetitive peak forward current	I _{F,max}	T _C =25 °C, t _p =10 μs	300		
.2	[:2 -u	T _C =25 °C, t _p =8.3 ms	60	A ² s	
i t value	ji at	T _C =150 °C, t _p =8.3 ms	23		
Repetitive peak reverse voltage	V _{RRM}	T _j =25 °C	1200	V	
Diode <i>dv/dt</i> ruggedness	dv/dt	Turn-on slew rate, repetitive	50	V/ns	
Power dissipation	P _{tot}	T _C =25 °C	115	W	
Operating & storage temperature	T _C , T _{storage}	Continuous	-55135	°C	
Soldering temperature	T _{solder}	Wave soldering leads	260	°C	
Mounting torque		M3 Screw	1	N-m	

Electrical Characteristics, at T_i=25 °C, unless otherwise specified

Static Characteristics Per Leg	Symbol	Conditions		Values		
			min.	typ.	max.	Unit
DC blocking voltage	V _{DC}		1200	-	-	
Diode forward voltage	V _F	l _F =15А, Т _ј =25 °С	-	1.5	1.7	V
		l _F =15А, Т _ј =175 °С	-	2.5	2.8	
Reverse current	I _R	V _R =1,200V, T _j =25 °C	-	4.1	100	μΑ
		V _R =1,200V, T _j =175 °C	-	1679	-	

1200V SiC Schottky Diode		<i>Amp</i> + [™]		GDP30D120B		
Parameter	Symbol	Conditions	Values			Unit
Falameter			min.	typ.	max.	Unit
AC Characteristics Per Leg						
Total capacitive charge	Q _{rr}	V _R =1,200V, T _j =27 °C	-	52	-	nC
Switching time	t _C	di _F /dt=200 A/µs T _j =150 °C	-	-	<10	ns
Total capacitance		V _R =1 V, f=1 MHz	-	895	-	pF
	С	V _R =600V, f=1 MHz	-	52	-	
		V _R =1,200V, f=1 MHz	-	43	-	

Thermal Characteristics Per Leg

Thermal resistance, junction-case	R _{thJC}	Package (flange) mount	-	1.30	-	°C/W

Typical Performance Per Leg

Forward Characteristics (parameterized on T_j)



Reverse Characteristics (parameterized on Tj)



Power Derating



Current Derating



1200V SiC Schottky Diode

Amp +[™]





Package Dimensions

Package TO-247-3 A 8 øP **⊕**0,635@BA E3 8 5 5 1 0 0.095 E1 0.81 7.69 1.35 16.13 14.15 5.10 502 5 b1 13.10 ٦ b3 2.60 0.780 20.32 0.80 0.14 2x e ^b ⊕0,254 @8A

Note RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.gptechgroup.com.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemi- cal Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at GPTG Headquarters in Lake Forest, California to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control.

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